

Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Application Number	New Application
				Filing Date	March 31, 2004
				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2826
				Examiner Name	S. Wilson
Sheet	1	of	1	Attorney Docket Number	740756-2719

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
T.D.		US-5,861,656	01/19/1999	Keri	
		US-5,471,330	11/28/1995	Sarma	
		US-6,147,667	11/14/2000	Yamazaki et al	
		US-5,767,531	06/16/1998	Yoshinouchi	
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		US-5,763,301	06/09/1998	Rha et al	
		US-5,818,067	10/06/1998	Rha et al	
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T.D.		US-5,471,330	11/28/1995	Sarma	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>2</sup> (if known)				
T.D.		JP 07-142734-A	06/02/1995			Abstract
T.D.		JP 58-163722-A	09/28/1983	Yabuki et al		Abstract
T.D.		JP 61-070780-A	04/11/1986	Oda et al		Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
T.D.		Lim et al. "High Performance Amorphous Silicon Thin Film Transistor with a Planarized SiN <sub>x</sub> /BCB Double-Layered Gate Insulator", AM-LCD '98 pp. 73-76	
T.D.		Won et al. "28.3: A High-Resolution Full Color TFT-LCD on Transparent Plastic", SID 03 DIGEST, pp. 992-995	
T.D.		Jang et al. "32.1: Invited Paper: Amorphous Silicon Thin-Film Transistors with Planarized Gate Insulators" (4 pages)	
T.D.		Wolf, Silicon Processing for the VLSI Era, 1990, Lattice Press, Volume 2, p. 273-274, 354, <del>356-357, 359</del> , 356-359	

Examiner Signature	<i>Wing Dang</i>	Date Considered	1/06/2005
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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